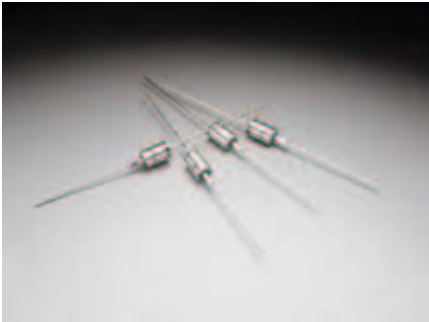




Part: 1N5649A
Series: OBSOLETE - 1N56 Series - 1500W Hermetically Sealed Metal TVS Diode For Harsh Industrial Applications
Technology:Silicon Avalanche Diode (SADs)

PARAMETERS		
Package Type	Pkg Type	Axial Leaded
Mount Method	Mount	Through Hole
Maximum Reverse Leakage Current	I R	0.00
Maximum Temperature	Max Temp (Å°C)	48.00
Standoff Polarity	Polarity	Unipolar
Tolerance	Tolerance	5
Breakover Voltage	V BO MIN (V)	0.00
Maximum Breakover Voltage	V BO MAX (V)	0.00
On-state forward Voltage	V F (V)	0.00
Minimum Foldback Voltage	V FB	0.00
Reverse Standoff Voltage	V SO	40.20
Device Wattage	Watts	1500
AC Working Voltage	VAC	0
Reverse Stand-off Voltage	V R (V)	40.20
Breakdown Voltage @ I_T	V BR MIN (V)	44.70
Breakdown Voltage @ I_T	V BR MAX (V)	49.40
Test Current	I T (mA)	1.00
Clamping Voltage	V CL @ I PP (ÅµA)	64.80
Peak Pulse Current	I PP 10x1000(A)	23.20
Peak Pulse Current	I PP 8x20 (A)	
Max Capacitance	C TYP (pF)	0
Working Inverse Blocking Voltage	V WIB (V)	0.00
Inverse Blocking Leakage Current	I IB @ V WIB (ÅµA)	0.00
Peak Inverse Blocking Voltage	V PIB (V)	0.00
Peak Pulse Current	I PP (A)	23.20
Minimum Zener Voltage @ I_Z	V Z MIN (V)	0.00
Maximum Zener Voltage @ I_Z	V Z MAX (V)	0.00
Zener Current	I Z (A)	0.00
Zener Resistance	Resistance (Ohms)	0.00
Peak Pulse Power - 10x1000Åµs	P PP 10x1000Åµs (W)	1500
Peak Pulse Power - 8x20Åµs	P PP 8x20Åµs (W)	0
Peak Pulse Power - 10x160Åµs	P PP 10x160Åµs (W)	0
Battery/System Voltage 12/14	Volt 12/14	
Battery/System Voltage 24/28	Volt 24/28	
Battery/System Voltage 36/42	Volt 36/42	Y



OBSOLETE 2004-06-01